40V; 2A NPN Low V_{CE(sat)} (BISS) Transistor

FEATURES

- Low collector-emitter saturation voltage
- High current capability
- Improved device reliability due to reduced heat generation.

APPLICATIONS

- Supply line switching circuits
- Battery management applications
- DC/DC converter applications
- Strobe flash units
- Heavy duty battery powered equipment (motor and lamp drivers).

Absolute Maximum Ratings (T_a = 25 °C)

STATE I			Symbol	Value	Unit	
Collector Base Voltage			V _{CBO}	40	V	
Collector Emitter Voltage			V _{CEO}	40	ISC V	
Emitter Base Voltage			V _{EBO}	5	V	
Collector Current (DC)			Ic	2	A	
Peak Collector Current			I _{CM}	3	А	
Peak Base Current			I _{BM}	300	mA	
Total Power Dissipation	$T_{amb} {\leq} 25^{\circ}C^{1)}$		- P _{tot}	200	mW	
	$T_{amb}{\leq}25^{\circ}C^{2)}$			480		
Junction Temperature			TJ	150	o 190 ∘C	
Storage Temperature Range			T _S	-65 to +150	°C	
Thermal Resistance From JunctionIn free air 1)to AmbientIn free air 2)			417			
		In free air ²⁾	R _{th j-a}	260	K/W	
Operating Ambient Temperature			T _{amb}	-65 to +150	٥C	

¹⁾ Device mounted on a printed-circuit board; single sided copper; tinplated and standard footprint.

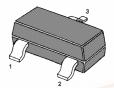
²⁾ Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1cm².



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)





SOT-23

1.BASE 2.EMITTER 3.COLLECTOR

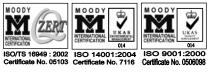
PBSS4240 查询"PBSS4240"供应商

Characteristics at Tamb=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V_{CE} =2V, I _C =100mA	h _{FE}	350	-	-	
at V_{CE} =2V, I _C =500mA	h _{FE}	300	-	-	-
at V_{CE} =2V, I _C =1A	h _{FE}	250	-	-	
at V_{CE} =2V, I _C =2A	h _{FE}	80	-	-	
Collector-Base Cutoff Current					
at V _{CB} =30V	I _{CBO}	-	-	100	nA
at V _{CB} =30V,T _{amb} =150 $^{\circ}$ C		-	-	50	μA
Emitter-Base Cutoff Current					
at V _{EB} =4V	I _{EBO}	-	-	100	nA
Collector-Emitter Saturation Voltage					
at I _C =100mA, I _B =1mA		-	-	70	mV
at I_C =500mA, I_B =50mA		-	-	100	
at I_{C} =750mA, I_{B} =15mA	V _{CE(sat)}	-	-	180	
at I_c =1A, I_B =50mA		-	-	180	
at $I_C=2A$, $I_B=200mA$		-	-	320	
Equivalent on-Resistance					
at I_{C} =500mA, I_{B} =50mA	R _{CE(sat)}	-	140	<200	mΩ
Base-Emitter Saturation Voltage					
at $I_c=2A$, $I_B=200mA$	V _{BE(sat)}	-	-	1.1	V
Base-Emitter Turn-on Voltage					
at V_{CE} =2V, I_C =100mA	$V_{BE(on)}$	-	-	0.75	V
Transition Frequency					
at V _{CE} =10V, I _C =100mA,f=100MHz	f⊤	100	230	-	MHz
Collector Capacitance					
at V _{CB} =10V, f=1MHz	Cc	-	15	20	pF







Dated : 20/10/2005